

Victor Makhniy

List of Publications by Year in descending order

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49
papers

80
citations

2258059

3
h-index

1720034

7
g-index

49
all docs

49
docs citations

49
times ranked

61
citing authors

#	ARTICLE	IF	CITATIONS
1	Current transport mechanisms in InSe/CdTe heterojunctions. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 3622-3625.	0.8	15
2	Preparation of II-VI and IV-VI semiconductor films for solar cells by the isovalent substitution technique with a CBD-made substrate. <i>Inorganic Materials</i> , 2014, 50, 546-550.	0.8	11
3	Isovalent substitution: a perspective method of producing heterojunction optoelectronic devices. , 2001, 4425, 272.		7
4	Optoelectronic properties of Ni-GaP diodes with a modified surface. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2016, 83, 227-231.	2.7	7
5	Specific features of the physical properties of a modified CdTe surface. <i>Semiconductors</i> , 2005, 39, 792-794.	0.5	3
6	The origin of edge luminescence in diffusion ZnSe:Sn layers. <i>Semiconductors</i> , 2007, 41, 784-785.	0.5	3
7	Mechanism of tin diffusion in ZnTe single crystals. <i>Inorganic Materials</i> , 2011, 47, 945-946.	0.8	3
8	Perspective of surface modification of CdTe single crystal substrate for creation of photosensitive barrier structures. <i>Semiconductor Physics, Quantum Electronics and Optoelectronics</i> , 2009, 12, 143-146.	1.0	3
9	"PURIFICATION EFFECTS" IN ZINC SELENIDE CRYSTALS DOPED WITH YTTERBIUM FROM VAPOR PHASE. <i>Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika)</i> , 2016, 75, 279-284.	0.4	3
10	Surface barrier diode based on zinc selenide with a passivating zinc oxide film. <i>Technical Physics Letters</i> , 2003, 29, 712-713.	0.7	2
11	Green luminescence in diffusion-doped layers of zinc selenide. <i>Technical Physics</i> , 2004, 49, 798-799.	0.7	2
12	Luminescence of zinc oxide layers synthesized on zinc selenide substrates by the isovalent substitution method. <i>Russian Physics Journal</i> , 2009, 52, 216-217.	0.4	2
13	Semimagnetic semiconductor oxides as materials for transparent electronics and spintronics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009, 206, 2177-2181.	1.8	2
14	Effect of heat treatment on the surface parameters of cadmium-telluride single-crystal substrates. <i>Journal of Surface Investigation</i> , 2013, 7, 562-564.	0.5	2
15	Thermal Annealing Effect on Optical Properties of the Cadmium Telluride Films. <i>Journal of Nano- and Electronic Physics</i> , 2017, 9, 05047-1-05047-3.	0.5	2
16	Semiconductor detectors for the erythema region of UV radiation. , 1999, , .		1
17	Electrical properties of UV detectors based on zinc selenide with modified surface barrier. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 1039-1043.	0.8	1
18	Mechanisms of photocurrent generation in $\text{In}_2\text{O}_3\text{-InSe}$ heterojunctions. <i>Semiconductors</i> , 2003, 37, 1387-1389.	0.5	1

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19	The nature of edge luminescence of CdTe:Mg diffusion layers. Semiconductors, 2010, 44, 1167-1169.	0.5	1
20	Effects of codoping in ZnO-based semimagnetic semiconductor thin films. IOP Conference Series: Materials Science and Engineering, 2010, 8, 012042.	0.6	1
21	Mechanism of ZnO heterolayer formation on ZnSe substrates. Inorganic Materials, 2011, 47, 746-748.	0.8	1
22	UV detector with internal gain based on SnO ₂ -ZnSe heterostructure. Technical Physics Letters, 2011, 37, 354-355.	0.7	1
23	Determination of the ionization energy of vanadium levels in zinc selenide. Semiconductors, 2012, 46, 141-142.	0.5	1
24	Optical absorption spectra as a useful tool to find parameters of deep impurity centers in semiconductors. Applied Optics, 2014, 53, B8.	1.8	1
25	Electrophysical Properties of Zinc Selenide Diffusion Layers Doped with 3-D Elements from the Vapor Phase. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2007, 66, 1769-1774.	0.4	1
26	OPTICAL PROPERTIES OF ZnSe:V CRYSTALS. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2007, 66, 465-471.	0.4	1
27	Electrical Properties of Surface-Barrier Diodes Based on the CdTe Crystals with Modified Surface. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2007, 66, 1769-1774.	0.4	1
28	Mechanisms of Defect Formation for ZnSe with Isovalent Oxygen Impurity. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2007, 66, 465-471.	0.4	1
29	Electrical and photoelectrical behavior of Au/n-CdTe junctions. , 2001, 4413, 258.		0
30	<title>II-VI compounds wide-band barrier detectors of He-Ne laser</title>. , 2002, , .		0
31	<title>Photodetectors on the base of CdTe and on the base of InSe for optical coherent tomography</title>. , 2004, , .		0
32	<title>Semiconductor UV-radiation detectors for biology and medicine</title>. , 2006, 6254, 493.		0
33	<title>Surface-barrier sensors on basis of zinc selenide</title>. , 2007, , .		0
34	Luminescence of broad-band compounds of elements of groups II-VI with a tin impurity. Journal of Optical Technology (A Translation of Opticheskiy Zhurnal), 2012, 79, 123.	0.4	0
35	Hall effect in CdTe crystals doped with Sn from the vapor phase. Semiconductors, 2014, 48, 1432-1433.	0.5	0
36	Nature of the blue emission band in zinc selenide containing sulfur isovalent impurity. Semiconductors, 2014, 48, 1161-1162.	0.5	0

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37	Luminescence of (ZnSe:Al):Yb Crystals at 4.2 K. Semiconductors, 2019, 53, 310-312.	0.5	0
38	Photodetectors Based on the Gallium Phosphide-Arsenide Heterojunctions Produced by Isovalent Substitution Method. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz) Tj ETQq0 0 0.4 BT / Overlock 10 T	0.4	0
39	Defect Formation Mechanisms for ZnSe with Isovalent Oxygen Impurity. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2007, 66, 1205-1211.	0.4	0
40	FORMATION OF Ge NANOCRYSTALS BY ELECTRON BEAM EVAPORATION., 2007,,.		0
41	Formation and Properties of n-CdO/p-CdTe Heterojunction. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2008, 67, 1763-1768.	0.4	0
42	UV PHOTOELECTRIC DETECTOR WITH INCORPORATED INTERNAL GAIN. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2012, 71, 1381-1385.	0.4	0
43	PHYSICAL PROPERTIES OF ZnSe HETEROLAYERS OBTAINED BY IZOVALENT SUBSTITUTION. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2013, 72, 1893-1897.	0.4	0
44	PHYSICAL PROPERTIES OF CdSe HETEROLAYERS WITH ISOVALENT TELLURIUM IMPURITY. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2013, 72, 741-744.	0.4	0
45	Î±-CdTe LAYERS: GROWING AND OPTICAL PROPERTIES. Telecommunications and Radio Engineering (English) Tj ETQq1 1 0.784314 rg	0.4	0
46	PECULIARITIES OF THE OPTICAL PROPERTIES OF WIDE-GAP II-VI COMPOUNDS WITH Mg ISOVALENT IMPURITY. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2014, 73, 909-914.	0.4	0
47	Optical properties of ZnSe(Te) with ytterbium impurity. Applied Optics, 2016, 55, B1.	1.8	0
48	OPTICAL PROPERTIES OF Cd _{0.55} Mn _{0.45} Te FILMS WITH NANO-SCALE SURFACE FORMATIONS. Telecommunications and Radio Engineering (English Translation of Elektrosvyaz and Radiotekhnika), 2017, 76, 865-871.	0.4	0
49	Preparation and Optical Properties of Substrates with Surface Nanostructure. Journal of Nano- and Electronic Physics, 2017, 9, 05026-1-05026-5.	0.5	0